

Description

The SX3400MI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 30V$ $I_D = 6.2A$

$R_{DS(ON)} < 25m\Omega$ @ $V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply

**Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)**

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^\circ C$	Continuous Drain Current	6.2	A
$I_D@T_A=70^\circ C$	Continuous Drain Current	4.9	A
I_{DM}	Pulsed Drain Current ²	20	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	125	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ ($t \leq 10s$)	85	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.029	---	$\text{V}/^\circ\text{C}$
$R_{DS(\text{ON})}$	Static Drain-Source On-Resistance ²	$V_{GS}=10\text{V}$, $I_D=5\text{A}$	---	21	25	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=3\text{A}$	---	23	31	
		$V_{GS}=2.5\text{V}$, $I_D=1\text{A}$	---	30	49	
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu\text{A}$	0.5	---	1.2	V
$\Delta V_{GS(\text{th})}$	$V_{GS(\text{th})}$ Temperature Coefficient		---	-2.82	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	1	uA
		$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$, $T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12\text{V}$, $V_{DS}=0\text{V}$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=5\text{A}$	---	25	---	S
R_g	Gate Resistance	$V_{DS}=0\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	1.5	---	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=15\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=5.8\text{A}$	---	11.5	---	nC
Q_{gs}	Gate-Source Charge		---	1.6	---	
Q_{gd}	Gate-Drain Charge		---	2.9	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15\text{V}$, $V_{GS}=10\text{V}$, $R_G=3\Omega$ $I_D=5\text{A}$	---	5	---	ns
T_r	Rise Time		---	47.	---	
$T_{d(off)}$	Turn-Off Delay Time		---	26	---	
T_f	Fall Time		---	8	---	
C_{iss}	Input Capacitance	$V_{DS}=15\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	530	---	pF
C_{oss}	Output Capacitance		---	130	---	
C_{rss}	Reverse Transfer Capacitance		---	36	---	
I_s	Continuous Source Current ^{1,4}	$V_G=V_D=0\text{V}$, Force Current	---	---	5.8	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0\text{V}$, $I_s=1\text{A}$, $T_J=25^\circ\text{C}$	---	---	1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

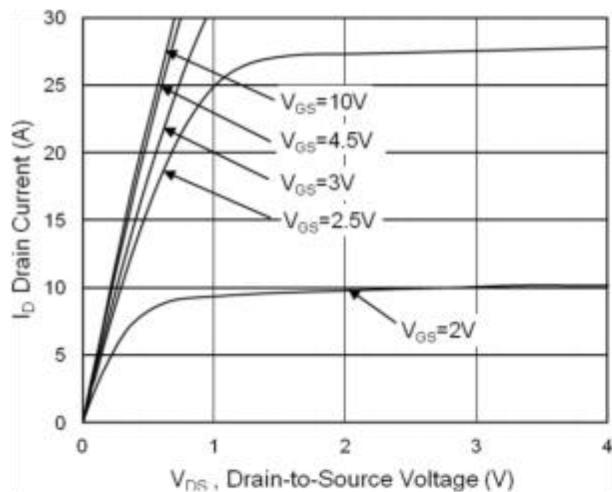


Fig.1 Typical Output Characteristics

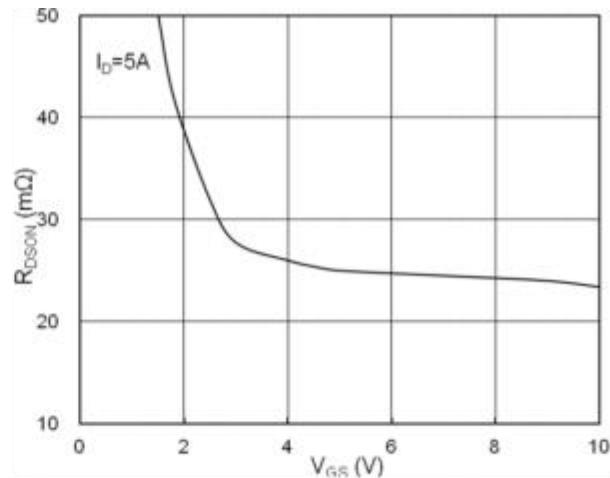


Fig.2 On-Resistance vs. Gate-Source

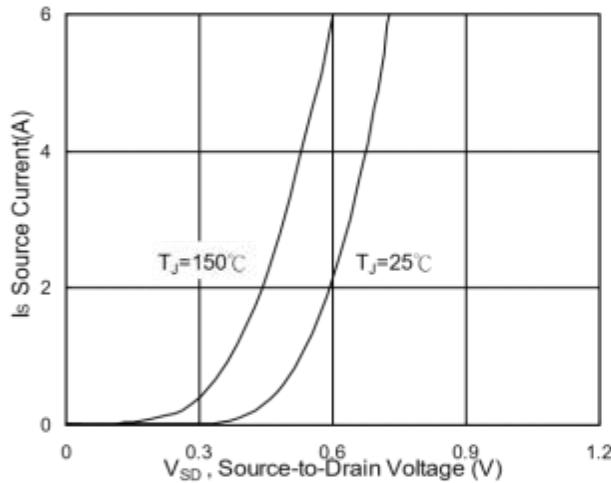


Fig.3 Forward Characteristics Of Reverse

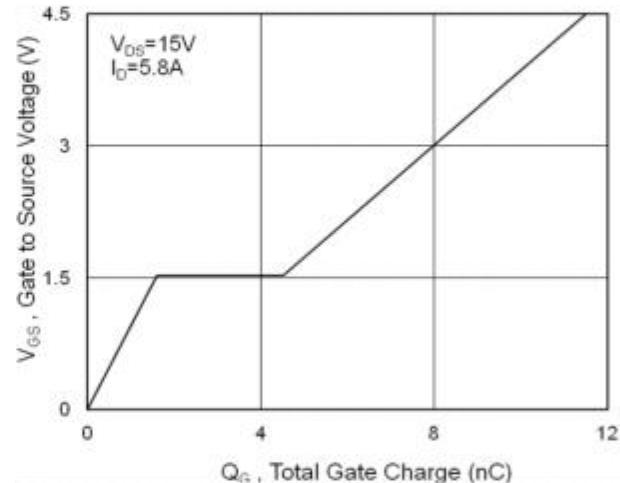


Fig.4 Gate-Charge Characteristics

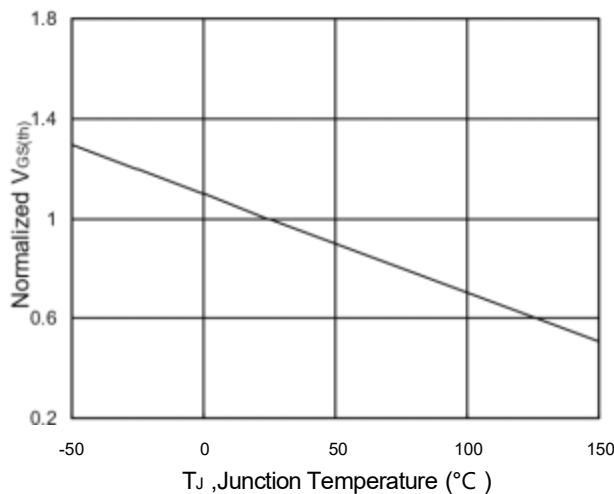


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

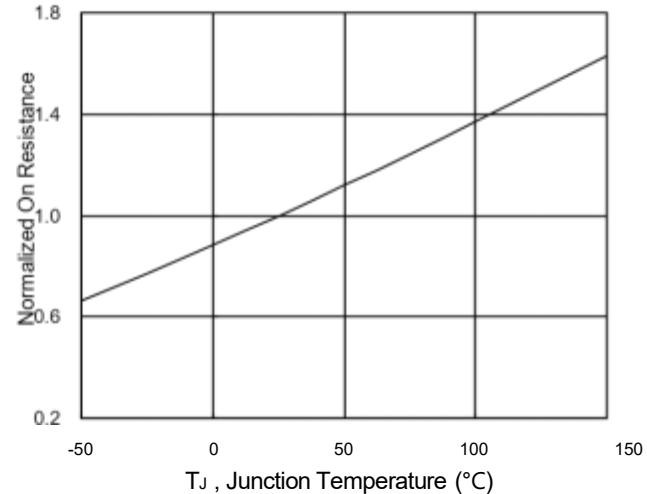


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

Typical Characteristics

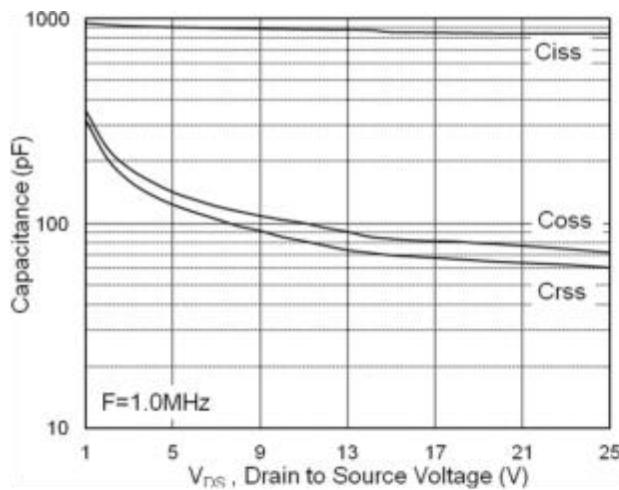


Fig.7 Capacitance

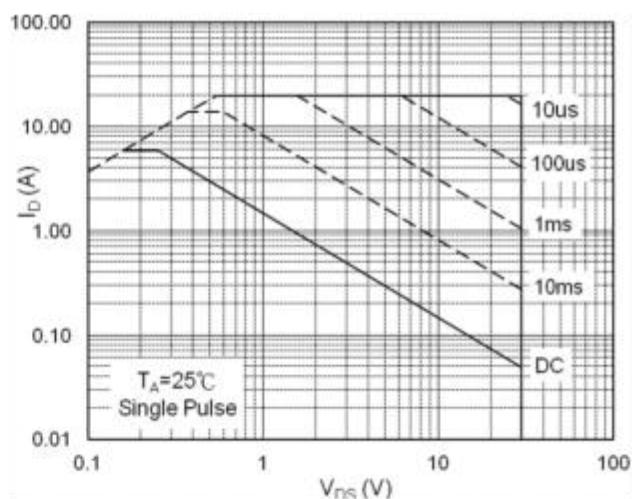


Fig.8 Safe Operating Area

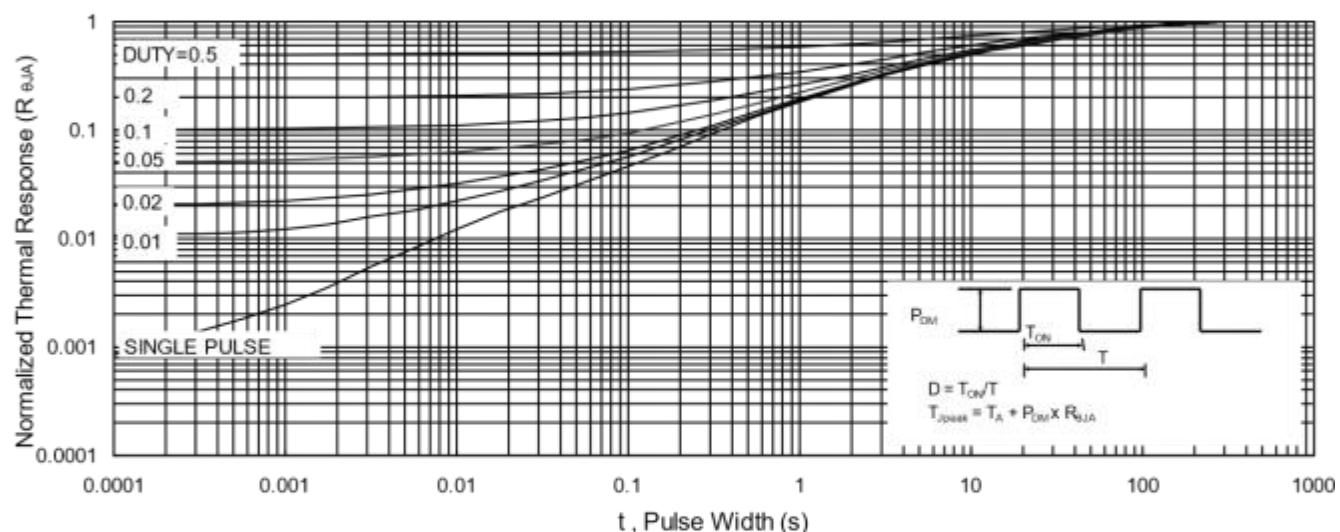


Fig.9 Normalized Maximum Transient Thermal Impedance

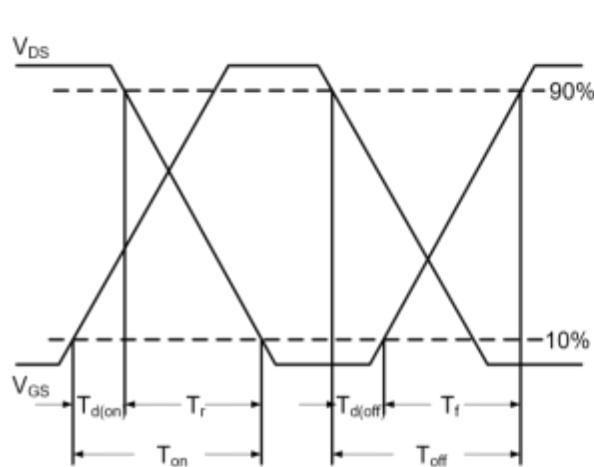


Fig.10 Switching Time Waveform

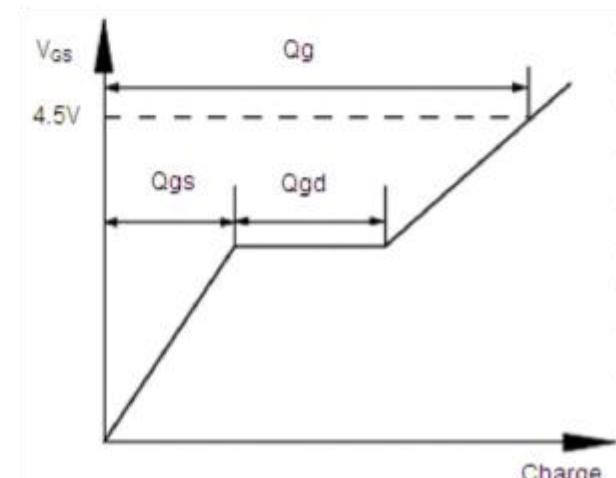
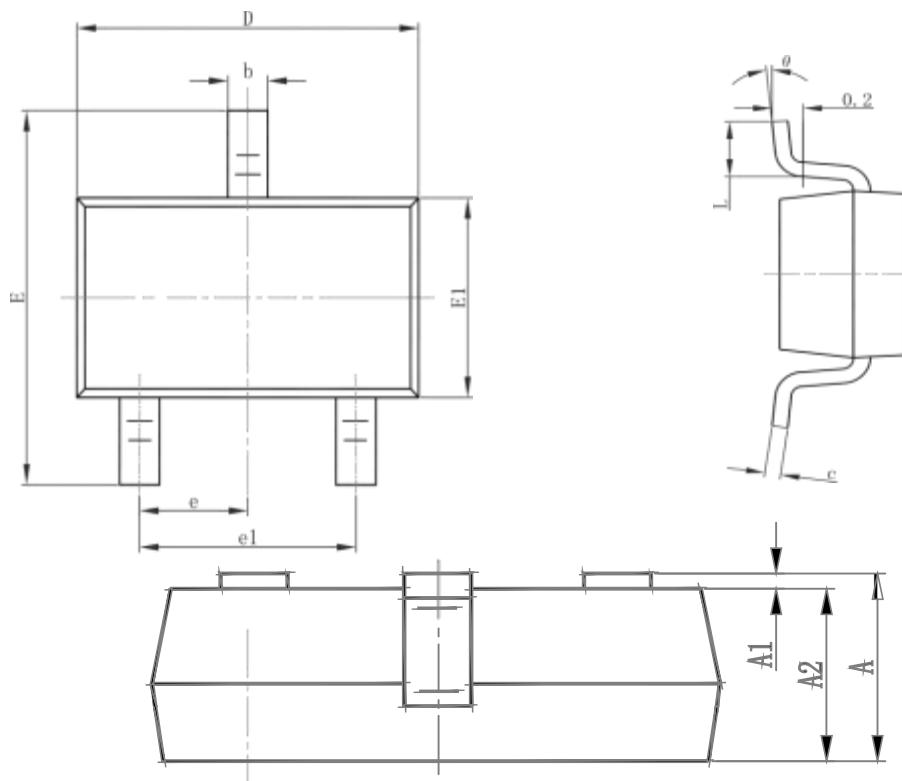


Fig.11 Gate Charge Waveform

Package Mechanical Data-SOT23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT-23-3L		3000